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The S-808 Series is a high-precision voltage detector developed using CMOS process. The detection voltage is fixed internally, with an accuracy of ±2.0%. Two output types, Nch open-drain and CMOS output, are available.

■ Features

• Ultra-low current consumption

1.3 μ A typ. (V_{DD}=1.5 V)

Products with detection voltage of 1.4 V or less electronic

 $0.8\mu A$ typ. $(V_{DD}=3.5 V)$

Products with detection voltage of 1.5,uor more

• High-precision detection voltage

±2.0%

· Low operating voltage

0.7 to 5.0 V

Products with detection voltage of 1.4,uor less

0.95 to 10.0 V

Products with a detection voltage of 1.5,uor more

• Hysteresis characteristics

5% typ.

Detection voltage

0.8 to 6.0 V

(0.1 V step)

• Nch open-drain active low and CMOS active low output

• SC-82AB Super-small plastic package

• TO-92 Plastic package

• SOT-89-3 Miniaturized power mold plastic package

• SOT-23-5 Very-small plastic package

■ Applications

- · Battery checker
- · Power failure detector
- Power monitor for pagers, calculators, organizers,
- Constant voltage power monitor for cameras, video equipment, communication devices
- Power monitor for microcomputers and reset CPUs

■ Pin Assignment

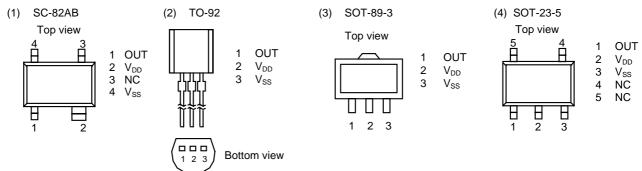


Figure 1

■ Block Diagram

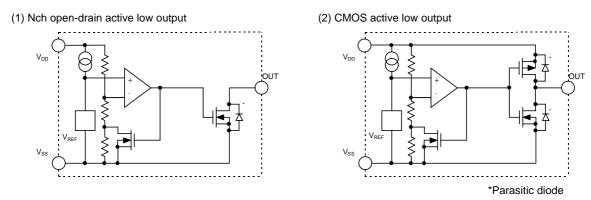


Figure 2

Selection Guide

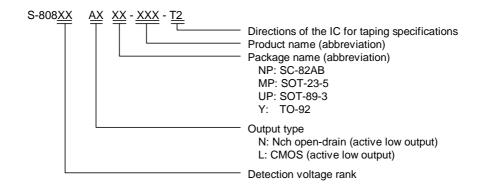


Table 1

		l able 1			
Detection voltage range	Hysteresis width		Nch Op	en Drain(Low)	T
(V)	V _{HYS} typ.(V)	SC-82AB	TO-92	SOT-89-3	SOT-23-5
0.8V±2.0%	0.034	S-80808ANNP-E7Y-T2	_	_	_
0.9V±2.0%	0.044	S-80809ANNP-E7Z-T2	_	_	_
1.0V±2.0%	0.054	S-80810ANNP-E70-T2		_	_
1.1V±2.0%	0.064	S-80811ANNP-E71-T2		_	_
1.2V±2.0%	0.073	S-80812ANNP-E72-T2	_	_	_
1.3V±2.0%	0.083	S-80813ANNP-EDA-T2		_	_
1.4V±2.0%	0.093	S-80814ANNP-EDB-T2		_	_
1.5V±2.0%	0.075	S-80815ANNP-EDC-T2	S-80815ANY	S-80815ANUP-EDC-T2	_
1.6V±2.0%	0.080	S-80816ANNP-EDD-T2	S-80816ANY	S-80816ANUP-EDD-T2	_
1.7V±2.0%	0.085	S-80817ANNP-EDE-T2	S-80817ANY	S-80817ANUP-EDE-T2	S-80817ANMP-EDE-T2
1.8V±2.0%	0.090	S-80818ANNP-EDF-T2	S-80818ANY	S-80818ANUP-EDF-T2	S-80818ANMP-EDF-T2
1.9V±2.0%	0.095	S-80819ANNP-EDG-T2	S-80819ANY	S-80819ANUP-EDG-T2	S-80819ANMP-EDG-T2
2.0V±2.0%	0.100	S-80820ANNP-EDH-T2	S-80820ANY	S-80820ANUP-EDH-T2	S-80820ANMP-EDH-T2
2.1V±2.0%	0.105	S-80821ANNP-EDJ-T2	S-80821ANY	S-80821ANUP-EDJ-T2	S-80821ANMP-EDJ-T2
2.2V±2.0%	0.110	S-80822ANNP-EDK-T2	S-80822ANY	S-80822ANUP-EDK-T2	S-80822ANMP-EDK-T2
2.3V±2.0%	0.115	S-80823ANNP-EDL-T2	S-80823ANY	S-80823ANUP-EDL-T2	S-80823ANMP-EDL-T2
2.4V±2.0%	0.120	S-80824ANNP-EDM-T2	S-80824ANY	S-80824ANUP-EDM-T2	S-80824ANMP-EDM-T2
2.5V±2.0%	0.125	S-80825ANNP-EDN-T2	S-80825ANY	S-80825ANUP-EDN-T2	S-80825ANMP-EDN-T2
2.6V±2.0%	0.130	S-80826ANNP-EDP-T2	S-80826ANY	S-80826ANUP-EDP-T2	_
2.7V±2.0%	0.135	S-80827ANNP-EDQ-T2	S-80827ANY	S-80827ANUP-EDQ-T2	S-80827ANMP-EDQ-T2
2.8V±2.0%	0.140	S-80828ANNP-EDR-T2	S-80828ANY	S-80828ANUP-EDR-T2	S-80828ANMP-EDR-T2
2.9V±2.0%	0.145	S-80829ANNP-EDS-T2	S-80829ANY	S-80829ANUP-EDS-T2	_
3.0V±2.0%	0.150	S-80830ANNP-EDT-T2	S-80830ANY	S-80830ANUP-EDT-T2	S-80830ANMP-EDT-T2
3.1V±2.0%	0.155	S-80831ANNP-EDV-T2	S-80831ANY	S-80831ANUP-EDV-T2	_
3.2V±2.0%	0.160	S-80832ANNP-EDW-T2	S-80832ANY	S-80832ANUP-EDW-T2	S-80832ANMP-EDW-T
3.3V±2.0%	0.165	S-80833ANNP-EDX-T2	S-80833ANY	S-80833ANUP-EDX-T2	S-80833ANMP-EDX-T2
3.4V±2.0%	0.170	S-80834ANNP-EDY-T2	S-80834ANY	S-80834ANUP-EDY-T2	S-80834ANMP-EDY-T2
3.5V±2.0%	0.175	S-80835ANNP-EDZ-T2	S-80835ANY	S-80835ANUP-EDZ-T2	S-80835ANMP-EDZ-T2
3.6V±2.0%	0.180	S-80836ANNP-ED0-T2	S-80836ANY	S-80836ANUP-ED0-T2	S-80836ANMP-ED0-T2
3.7V±2.0%	0.185	S-80837ANNP-ED1-T2	S-80837ANY	S-80837ANUP-ED1-T2	_
3.8V±2.0%	0.190	S-80838ANNP-ED2-T2	S-80838ANY	S-80838ANUP-ED2-T2	_
3.9V±2.0%	0.195	S-80839ANNP-ED3-T2	S-80839ANY	S-80839ANUP-ED3-T2	S-80839ANMP-ED3-T2
4.0V±2.0%	0.200	S-80840ANNP-ED4-T2	S-80840ANY	S-80840ANUP-ED4-T2	S-80840ANMP-ED4-T2
4.1V±2.0%	0.205	S-80841ANNP-ED5-T2	S-80841ANY	S-80841ANUP-ED5-T2	_
4.2V±2.0%	0.210	S-80842ANNP-ED6-T2	S-80842ANY	S-80842ANUP-ED6-T2	S-80842ANMP-ED6-T2
4.3V±2.0%	0.215	S-80843ANNP-ED7-T2	S-80843ANY	S-80843ANUP-ED7-T2	_
4.4V±2.0%	0.220	S-80844ANNP-ED8-T2	S-80844ANY	S-80844ANUP-ED8-T2	S-80844ANMP-ED8-T2
4.5V±2.0%	0.225	S-80845ANNP-ED9-T2	S-80845ANY	S-80845ANUP-ED9-T2	
4.6V±2.0%	0.230	S-80846ANNP-EJA-T2	S-80846ANY	S-80846ANUP-EJA-T2	_
4.7V±2.0%	0.235	S-80847ANNP-EJB-T2	S-80847ANY	S-80847ANUP-EJB-T2	_
4.8V±2.0%	0.240	S-80848ANNP-EJC-T2	S-80848ANY	S-80848ANUP-EJC-T2	_
4.9V±2.0%	0.245	S-80849ANNP-EJD-T2	S-80849ANY	S-80849ANUP-EJD-T2	_
5.0V±2.0%	0.250	S-80850ANNP-EJE-T2	S-80850ANY	S-80850ANUP-EJE-T2	S-80850ANMP-EJE-T2
5.1V±2.0%	0.255	S-80851ANNP-EJF-T2	S-80851ANY	S-80851ANUP-EJF-T2	S-80851ANMP-EJF-T2
5.2V±2.0%	0.260	S-80852ANNP-EJG-T2	—	S-80852ANUP-EJG-T2	_
5.3V±2.0%	0.265	S-80853ANNP-EJH-T2	S-80853ANY		_
5.4V±2.0%	0.270	S-80854ANNP-EJJ-T2	—	_	
5.5V±2.0%	0.275	S-80855ANNP-EJK-T2			
5.6V±2.0%	0.275	S-80856ANNP-EJL-T2		_	
5.6V±2.0% 5.7V±2.0%	0.285	S-80857ANNP-EJL-12			
			<u> </u>	_	_
5.8V±2.0%	0.290	S-80858ANNP-EJN-T2		_	_
5.9V±2.0%	0.295	S-80859ANNP-EJP-T2	_	S 80860 ANU ID E IO T2	_
6.0V±2.0%	0.300	S-80860ANNP-EJQ-T2	_	S-80860ANUP-EJQ-T2	

Detection voltage range	Hysteresis width		CMOS Ou	tput Drain(Low)	
(V)	V _{HYS} typ.(V)	SC-82AB	TO-92	SOT-89-3	SOT-23-5
0.8V±2.0%	0.034	S-80808ALNP-E5Y-T2	_	_	_
0.9V±2.0%	0.044	S-80809ALNP-E5Z-T2	_	_	_
1.0V±2.0%	0.054	S-80810ALNP-E50-T2	_	_	_
1.1V±2.0%	0.064	S-80811ALNP-E51-T2	_	_	_
1.2V±2.0%	0.073	S-80812ALNP-E52-T2	_	_	_
1.3V±2.0%	0.083	S-80813ALNP-EAA-T2	_	_	_
1.4V±2.0%	0.093	S-80814ALNP-EAB-T2	_	_	_
1.5V±2.0%	0.075	S-80815ALNP-EAC-T2	S-80815ALY	S-80815ALUP-EAC-T2	S-80815ALMP-EAC-T2
1.6V±2.0%	0.080	S-80816ALNP-EAD-T2	S-80816ALY	S-80816ALUP-EAD-T2	_
1.7V±2.0%	0.085	S-80817ALNP-EAE-T2	S-80817ALY	S-80817ALUP-EAE-T2	_
1.8V±2.0%	0.090	S-80818ALNP-EAF-T2	S-80818ALY	S-80818ALUP-EAF-T2	S-80818ALMP-EAF-T2
1.9V±2.0%	0.095	S-80819ALNP-EAG-T2	S-80819ALY	S-80819ALUP-EAG-T2	S-80819ALMP-EAG-T2
2.0V±2.0%	0.100	S-80820ALNP-EAH-T2	S-80820ALY	S-80820ALUP-EAH-T2	S-80820ALMP-EAH-T2
2.1V±2.0%	0.105	S-80821ALNP-EAJ-T2	S-80821ALY	S-80821ALUP-EAJ-T2	S-80821ALMP-EAJ-T2
2.2V±2.0%	0.110	S-80822ALNP-EAK-T2	S-80822ALY	S-80822ALUP-EAK-T2	_
2.3V±2.0%	0.115	S-80823ALNP-EAL-T2	S-80823ALY	S-80823ALUP-EAL-T2	S-80823ALMP-EAL-T2
2.4V±2.0%	0.120	S-80824ALNP-EAM-T2	S-80824ALY	S-80824ALUP-EAM-T2	_
2.5V±2.0%	0.125	S-80825ALNP-EAN-T2	S-80825ALY	S-80825ALUP-EAN-T2	S-80825ALMP-EAN-T2
2.6V±2.0%	0.130	S-80826ALNP-EAP-T2	S-80826ALY	S-80826ALUP-EAP-T2	_
2.7V±2.0%	0.135	S-80827ALNP-EAQ-T2	S-80827ALY	S-80827ALUP-EAQ-T2	S-80827ALMP-EAQ-T2
2.8V±2.0%	0.140	S-80828ALNP-EAR-T2	S-80828ALY	S-80828ALUP-EAR-T2	S-80828ALMP-EAR-T2
2.9V±2.0%	0.145	S-80829ALNP-EAS-T2	S-80829ALY	S-80829ALUP-EAS-T2	_
3.0V±2.0%	0.150	S-80830ALNP-EAT-T2	S-80830ALY	S-80830ALUP-EAT-T2	S-80830ALMP-EAT-T2
3.1V±2.0%	0.155	S-80831ALNP-EAV-T2	S-80831ALY	S-80831ALUP-EAV-T2	_
3.2V±2.0%	0.160	S-80832ALNP-EAW-T2	S-80832ALY	S-80832ALUP-EAW-T2	S-80832ALMP-EAW-T2
3.3V±2.0%	0.165	S-80833ALNP-EAX-T2	S-80833ALY	S-80833ALUP-EAX-T2	S-80833ALMP-EAX-T2
3.4V±2.0%	0.170	S-80834ALNP-EAY-T2	S-80834ALY	S-80834ALUP-EAY-T2	_
3.5V±2.0%	0.175	S-80835ALNP-EAZ-T2	S-80835ALY	S-80835ALUP-EAZ-T2	S-80835ALMP-EAZ-T2
3.6V±2.0%	0.180	S-80836ALNP-EA0-T2	S-80836ALY	S-80836ALUP-EA0-T2	_
3.7V±2.0%	0.185	S-80837ALNP-EA1-T2	S-80837ALY	S-80837ALUP-EA1-T2	_
3.8V±2.0%	0.190	S-80838ALNP-EA2-T2	S-80838ALY	S-80838ALUP-EA2-T2	_
3.9V±2.0%	0.195	S-80839ALNP-EA3-T2	S-80839ALY	S-80839ALUP-EA3-T2	_
4.0V±2.0%	0.200	S-80840ALNP-EA4-T2	S-80840ALY	S-80840ALUP-EA4-T2	S-80840ALMP-EA4-T2
4.1V±2.0%	0.205	S-80841ALNP-EA5-T2	S-80841ALY	S-80841ALUP-EA5-T2	_
4.2V±2.0%	0.210	S-80842ALNP-EA6-T2	S-80842ALY	S-80842ALUP-EA6-T2	S-80842ALMP-EA6-T2
4.3V±2.0%	0.215	S-80843ALNP-EA7-T2	S-80843ALY	S-80843ALUP-EA7-T2	_
4.4V±2.0%	0.220	S-80844ALNP-EA8-T2	S-80844ALY	S-80844ALUP-EA8-T2	1
4.5V±2.0%	0.225	S-80845ALNP-EA9-T2	S-80845ALY	S-80845ALUP-EA9-T2	S-80845ALMP-EA9-T2
4.6V±2.0%	0.230	S-80846ALNP-EEA-T2	S-80846ALY	S-80846ALUP-EEA-T2	1
4.7V±2.0%	0.235	S-80847ALNP-EEB-T2	S-80847ALY	S-80847ALUP-EEB-T2	1
4.8V±2.0%	0.240	S-80848ALNP-EEC-T2	S-80848ALY	S-80848ALUP-EEC-T2	_
4.9V±2.0%	0.245	S-80849ALNP-EED-T2	S-80849ALY	S-80849ALUP-EED-T2	S-80849ALMP-EED-T2
5.0V±2.0%	0.250	S-80850ALNP-EEE-T2	S-80850ALY	S-80850ALUP-EEE-T2	S-80850ALMP-EEE-T2
5.1V±2.0%	0.255	S-80851ALNP-EEF-T2	S-80851ALY	S-80851ALUP-EEF-T2	S-80851ALMP-EEF-T2
5.2V±2.0%	0.260	S-80852ALNP-EEG-T2		S-80852ALUP-EEG-T2	S-80852ALMP-EEG-T2
5.3V±2.0%	0.265	S-80853ALNP-EEH-T2	_	_	_
5.4V±2.0%	0.270	S-80854ALNP-EEJ-T2		_	
5.5V±2.0%	0.275	S-80855ALNP-EEK-T2	_	S-80855ALUP-EEK-T2	_
5.6V±2.0%	0.280	S-80856ALNP-EEL-T2		_	_
5.7V±2.0%	0.285	S-80857ALNP-EEM-T2	_	_	_
5.8V±2.0%	0.290	S-80858ALNP-EEN-T2	_	_	_
5.9V±2.0%	0.295	S-80859ALNP-EEP-T2	_	_	_
		S-80860ALNP-EEQ-T2		1	

Remark: Some products described here in are under development. Please contact us for Samples.

■ Output Configurations

1. S-808 Series model numbering system

	Nch open-drain	CMOS output
	("L" reset type)	("L" reset type)
S-808 Series	model number.	"L" is the last letter of the model number.
	e.g. S-80808AN	e.g. S-80808AL

2. Output configurations and their implementation

Implementation	Nch("L")	CMOS("L")
With different power supplies	Yes	No
With active low reset CPUs	Yes	Yes
With active high reset CPUs	No	No
With voltage divider variable resistors	Yes	No

- Example with two power supplies
- Examples with one power supply

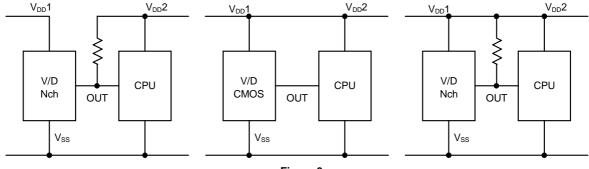


Figure 3

■ Absolute Maximum Ratings

1. Products with detection voltage of 1.4 V or less

	(Unless otherwise specified:			
Р	arameter	Symbol	Ratings	Unit
Power supp	ly voltage	V _{DD} - V _{SS}	7	V
Output voltage	Nch open-drain	V _{OUT}	V _{ss} -0.3 to 7	٧
	CMOS		V_{SS} -0.3 to V_{DD} +0.3	V
Output curre	ent	I _{OUT}	50	mA
Power dissipation		Pd	150	mW
Operating temperature		Topr	-20 to +70	°C
Storage tem	perature	Tstg	-40 to +125	°C

2. Products with detection voltage of 1.5 V or more

(Unless otherwise specified: Ta=25°C)

(enless differ wise specified: 14-					
Parameter		Symbol		Ratings	Unit
Power suppl	y voltage		V_{DD} - V_{SS}	12	V
Output voltage	Nch open-drain	V _{OUT}		V _{SS} -0.3 to 12	V
	CMOS			V_{SS} -0.3 to V_{DD} +0.3	V
Output curre	Output current		I _{OUT}	50	mA
			TO-92	400	
Power dissip	ation	Pd	SOT-89-3	500	mW
			SC-82AB,SOT-23-5	150	
Operating temperature			Topr	-40 to +85	°C
Storage temperature			Tstg -40 to +125		°C

Remark: This IC has a built-in protection circuit for static electricity. However, prevent contact with a large static electricity or electrostatic voltage which exceeds the performance of the protection circuit

■ Electrical Characteristics

1. Detection voltage (0.8 V to 1.4 V)

Parameter	Symbol	Cond	ditions	Min.	Inless othe Typ.	Max.	Unit	Test circuit
			S-80808AX	0.784	0.800	0.816		
			S-80809AX	0.882	0.900	0.918		
			S-80810AX	0.980	1.000	1.020		
Detection voltage	$-V_{DET}$		S-80811AX	1.078	1.100	1.122	٧	1
			S-80812AX	1.176	1.200	1.224		
			S-80813AX	1.274	1.300	1.326		
			S-80814AX	1.372	1.400	1.428		
			S-80808AX	0.802	0.834	0.867		
			S-80809AX	0.910	0.944	0.979		
			S-80810AX	1.017	1.054	1.091		
Release voltage	$+V_{DET}$		S-80811AX	1.125	1.164	1.203	V	1
			S-80812AX	1.232	1.273	1.315		
			S-80813AX	1.340	1.383	1.427		
			S-80814AX	1.448	1.493	1.538		
			S-80808AX	0.018	0.034	0.051		
			S-80809AX	0.028	0.044	0.061		
			S-80810AX	0.037	0.054	0.071		
Hysteresis width	V_{HYS}		S-80811AX	0.047	0.064	0.081	V	1
			S-80812AX	0.056	0.073	0.091		
			S-80813AX	0.066	0.083	0.101		
			S-80814AX	0.076	0.093	0.110		
		V _{DD} =1.5V	S-80808AX					
			S-80809AX					
			S-80810AX					
Current			S-80811AX		1.3	2.7	^	2
consumption	I _{SS}	.,	S-80812AX	_	1.3	3.7	μΑ	2
·		V _{DD} =2.0V						
			S-80813AX					
			S-80814AX					
Operating voltage	V_{DD}			0.7	_	5.0	V	1
		Nch	$V_{DS}=0.5V$	0.04	0.2	_		3
Output current	I _{OUT}		$V_{DD}=0.7V$				mA	
		Pch(CMOS	V _{DS} =2.1V	2.9	5.8	_		4
		output)	V _{DD} =4.5V					
Leakage current of output transistor	I_{LEAK}	Nch(Nch open drain)	V_{DS} =5.0V V_{DD} =5.0V	_	_	60	nA	3
			S-80808AX	_	±0.18	_		
			S-80809AX	_	±0.20	_]	
Temperature	Δ -V _{DET}	Ta=-20°C	S-80810AX	_	±0.22	_	mV/°C	1
characteristic of	∆Ta	to +70°C	S-80811AX	_	±0.24	_	1	
-V _{DET}			S-80812AX		±0.27	_		
		-	S-80813AX		±0.29			

2. Detection voltage (1.5 V to 2.6 V)

/1.1	- 0		T- 0500\
(Unless	otnerwise	specified:	Ta=25°C)

Parameter	Symbol	Conc	ditions	Min.	Typ.	Max.	Unit	Test
1 diameter	Cyllibol	Oone			• •		Offic	circuit
			S-80815AX	1.470	1.500	1.530		
			S-80816AX	1.568	1.600	1.632		
			S-80817AX	1.666	1.700	1.734		
			S-80818AX	1.764	1.800	1.836		
			S-80819AX	1.862	1.900	1.938		
Detection voltage	-V _{DET}		S-80820AX	1.960	2.000	2.040	V	1
			S-80821AX	2.058	2.100	2.142		
			S-80822AX	2.156	2.200	2.244		
			S-80823AX	2.254	2.300	2.346		
			S-80824AX	2.352	2.400	2.448		
			S-80825AX	2.450	2.500	2.550		
			S-80826AX	2.548	2.600	2.652		
Hysteresis width	V _{HYS}			-V _{DET} ×0.03	-V _{DET} ×0.05	-V _{DET} ×0.08	V	1
Current consumption	I _{SS}	V _{DD} =3.5V		_	0.8	2.4	μΑ	2
Operating voltage	V_{DD}			0.95	_	10.0	V	1
		Nch	V _{DD} =1.2V	0.23	0.50	_		3
Output current		V _{DS} =0.5V						
	I _{OUT}	Pch(CMOS					mA	
		output)	$V_{DD}=4.8V$	0.36	0.62	_		4
		V _{DS} =0.5V						
Leakage current of	I _{LEAK}	Nch(Nch	V _{DS} =10.0	_	_	0.1	μΑ	3
output transistor		open drain)	v V _{DD} =10.0					
			V					
Response time	tPLH	1			_	60	μs	1
			S-80815AX	_	±0.18	±0.54		
			S-80816AX	_	±0.19	±0.57		
			S-80817AX	_	±0.20	±0.60		
			S-80818AX	_	±0.21	±0.63		
Temperature			S-80819AX	_	±0.22	±0.66		
characteristic of	Δ -V _{DET}	Ta=-40°C	S-80820AX		±0.24	±0.72	mV/°C	1
-V _{DET}	∆Ta	to +85°C	S-80821AX		±0.25	±0.75		
			S-80822AX		±0.26	±0.78	•	
			S-80823AX		±0.27	±0.81		
			S-80824AX		±0.28	±0.84		
			S-80825AX	_	±0.29	±0.87		
			S-80826AX	_	±0.31	±0.93		

3. Detection voltage (2.7 V to 3.9 V)

1				(Unless othe	erwise spe	cified: Ta:	
Parameter	Symbol	Cond	ditions	Min.	Тур.	Max.	Unit	Test circuit
			S-80827AX	2.646	2.700	2.754		
			S-80828AX	2.744	2.800	2.856		
			S-80829AX	2.842	2.900	2.958		
			S-80830AX	2.940	3.000	3.060		
			S-80831AX	3.038	3.100	3.162		
			S-80832AX	3.136	3.200	3.264		
Detection voltage	$-V_{DET}$		S-80833AX	3.234	3.300	3.366	V	1
			S-80834AX	3.332	3.400	3.468		
			S-80835AX	3.430	3.500	3.570		
			S-80836AX	3.528	3.600	3.672		
			S-80837AX	3.626	3.700	3.774		
			S-80838AX	3.724	3.800	3.876		
			S-80839AX	3.822	3.900	3.978		
Hysteresis width	V_{HYS}			-V _{DET} 0.03	-V _{DET} ×0.05	-V _{DET} ×0.08	V	1
Current consumption	I _{SS}	V _{DD} =4.5V		_	0.9	2.7	μΑ	2
Operating voltage	V_{DD}			0.95	_	10.0	V	1
		Nch	V _{DD} =1.2V	0.23	0.50	_		
Output current		V _{DS} =0.5V	V _{DD} =2.4V	1.60	3.70	_	1	3
·	I _{OUT}	Pch(CMOS output) V _{DS} =0.5V	V _{DD} =4.8V	0.36	0.62	_	mA	4
Leakage current of output transistor	I _{LEAK}	Nch(Nch open drain)	V _{DS} =10.0 V V _{DD} =10.0 V	_	_	0.1	μА	3
Response time	tPLH				_	60	μs	1
			S-80827AX	_	±0.32	±0.96		
			S-80828AX	_	±0.33	±0.99		
			S-80829AX	_	±0.34	±1.02		
			S-80830AX	_	±0.35	±1.05		
Temperature			S-80831AX	_	±0.36	±1.08		
characteristic of	Δ -V _{DET}	Ta=-40°C	S-80832AX	_	±0.38	±1.14	mV/°C	1
-V _{DET}	<u>∆</u> Ta	to +85°C	S-80833AX		±0.39	±1.17	†	
	ıα		S-80834AX		±0.40	±1.20	1	
			S-80835AX		±0.41	±1.23	1	
			S-80836AX	_	±0.42	±1.26	1	
			S-80837AX		±0.44	±1.32	1	
			S-80838AX	_	±0.45	±1.35	1	
		1	3 333007 170		_0.40	200]	

4. Detection voltage (4.0 V to 5.6 V)

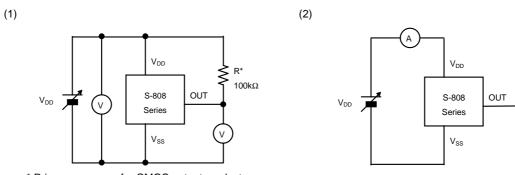
(Linlage	othorwica	enacified.	Ta=25°C)
TUTILESS	otherwise	specified.	1a=25 C)

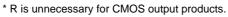
Т		1	1		Unless othe I	i wise spec	Jilieu. Ta	Test
Parameter	Symbol	Cond	ditions	Min.	Тур.	Max.	Unit	circuit
			S-80840AX	3.920	4.000	4.080		
			S-80841AX	4.018	4.100	4.182		
			S-80842AX	4.116	4.200	4.284		
			S-80843AX	4.214	4.300	4.386		
			S-80844AX	4.312	4.400	4.488		
			S-80845AX	4.410	4.500	4.590		
			S-80846AX	4.508	4.600	4.692		
			S-80847AX	4.606	4.700	4.794		
Detection voltage	$-V_{DET}$		S-80848AX	4.704	4.800	4.896	V	1
			S-80849AX	4.802	4.900	4.998		
			S-80850AX	4.900	5.000	5.100		
			S-80851AX	4.998	5.100	5.202		
			S-80852AX	5.096	5.200	5.304		
			S-80853AX	5.194	5.300	5.406		
			S-80854AX	5.292	5.400	5.508		
			S-80855AX	5.390	5.500	5.610		
			S-80856AX	5.488	5.600	5.712		
Hysteresis width	V_{HYS}			-V _{DET} ×0.03	-V _{DET} ×0.05	-V _{DET} ×0.08	V	1
Current consumption	I_{SS}	V _{DD} =6.0V		_	1.0	3.0	μΑ	2
Operating voltage	V_{DD}			0.95	_	10.0	V	1
	_	Nch	V _{DD} =1.2V	0.23	0.50	_		
			V _{DD} =2.4V	1.60	3.70	_		3
Output current	I _{OUT}	Pch(CMOS					mA	_
		output)	$V_{DD}=6.0V$	0.46	0.75	_		4
Leakage current of		V _{DS} =0.5V Nch(Nch	V _{DS} =10.0			0.4		2
output transistor	I_{LEAK}	open drain)	V	_	_	0.1	μΑ	3
			V _{DD} =10.0 V					
Response time	tPLH		-	_	_	60	μs	1
			S-80840AX		±0.47	±1.41		
			S-80841AX		±0.48	±1.44		
			S-80842AX	_	±0.49	±1.47		
			S-80843AX		±0.51	±1.53		
			S-80844AX		±0.52	±1.56		
			S-80845AX		±0.53	±1.59		
Temperature			S-80846AX		±0.54	±1.62		
characteristic of	Δ -V _{DET}	Ta=-40°C	S-80847AX	_	±0.55	±1.65	mV/°C	1
-V _{DET}	∆Та	to +85°C	S-80848AX	_	±0.56	±1.68		
			S-80849AX	_	±0.58	±1.74	1	
			S-80850AX	_	±0.59	±1.77	1	
			S-80851AX	_	±0.60	±1.80	1	
			S-80852AX	_	±0.61	±1.83	1	
			S-80853AX	_	±0.62	±1.86	1	
			S-80854AX	_	±0.64	±1.92	1	
			S-80855AX	_	±0.65	±1.95	1	
			S-80856AX	_	±0.66	±1.98		
<u>ı</u>		1 1			1		1	

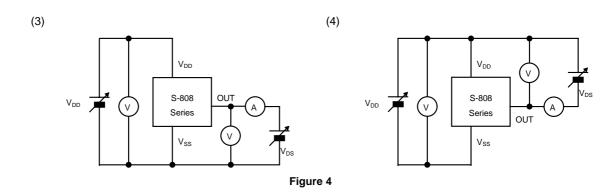
5. Detection voltage (5.7 V to 6.0 V)

		(Unless otherwise specified: Ta								
Parameter	Symbol	Cond	ditions	Min.	Тур.	Max.	Unit	Test circuit		
			S-80857AX	5.586	5.700	5.814				
Detection voltage	-V _{DET}		S-80858AX	5.684	5.800	5.916	V	1		
			S-80859AX	5.782	5.900	6.018				
			S-80860AX	5.880	6.000	6.120				
Hysteresis width	V _{HYS}			-V _{DET} ×0.03	-V _{DET} ×0.05	-V _{DET} ×0.08	V	1		
Current consumption	I _{SS}	V _{DD} =7.5V		_	1.0	3.0	μΑ	2		
Operating voltage	V_{DD}			0.95	_	10.0	V	1		
		Nch	V _{DD} =1.2V	0.23	0.50	_				
		$V_{DS}=0.5V$	V _{DD} =2.4V	1.60	3.70	_		3		
Output current	I _{OUT}	Pch(CMOS output) V _{DS} =0.5V	V _{DD} =8.4V	0.59	0.96	_	mA	4		
Leakage current of output transistor	I _{LEAK}	Nch(Nch open drain)	V _{DS} =10.0 V V _{DD} =10.0 V	_	_	0.1	μА	3		
Response time	tPLH			_	_	60	μs	1		
			S-80857AX	_	±0.67	±2.01				
Temperature	Δ -V _{DET}	Ta=-40°C	S-80858AX	_	±0.68	±2.04	mV/°C	1		
characteristic of	≙Ta	to +85°C	S-80859AX	_	±0.69	±2.07				
-V _{DET}			S-80860AX	_	±0.71	±2.13				

■ Test Circuits







■ Technical Terms

1. Detection voltage (-V_{DET})

The detection voltage $-V_{DET}$ is the voltage at which the output switches to low. This detection voltage varies slightly among products of the same type. The variation of voltages between the specified minimum [(- V_{DET})min.] and maximum [(- V_{DET})max.] values is called the detection voltage range (See Figure 5).

Example: For the S-80808AN, detection voltage lies in the range of 0.784 ≤ (-V_{DET}) ≤ 0.816.

This means that -V_{DET} is 0.784 in a product while -V_{DET} is 0.816 in another of the same S-80808AN.

2. Release voltage (+V_{DET})

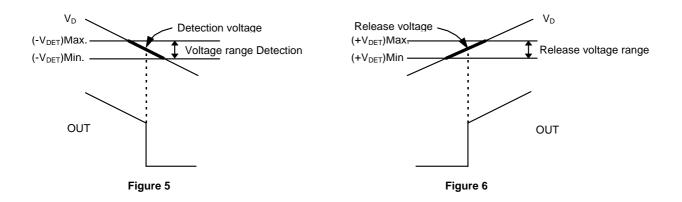
The release voltage $+V_{DET}$ is the voltage at which the output returns (is "released") to high. This release voltage varies slightly among products of the same type. The variation of voltages between the specified minimum [($+V_{DET}$)min.] and maximum [($+V_{DET}$)max.] values is called the release voltage range (See Figure 6).

Example: For the S-80808AN, the release voltage lies in the range of $0.802 \le (+V_{DET}) \le 0.867$. This means that

+V_{DET} is 0.802 in a product while +V_{DET} is 0.867 in another of the same S-80808AN.

Remark: Although the detection voltage and release voltage overlap in the range of 0.802 V to 0.816 V, +V_{DET} will

always be larger than -V_{DET}.



3. Hysteresis width (V_{HYS})

The hysteresis width is the voltage difference between the detection voltage and the release voltage (B-A=V_{HYS} in Figure 10). By giving a device hysteresis, trouble such as noise at the input is avoided.

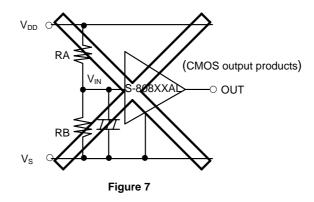
4. Through-type current

Through-type current refers to the current which flows instantaneously at the time of detection and release of a voltage detector. Through-type current is large in CMOS output devices, and also flows to some extent in Nch open-drain output devices.

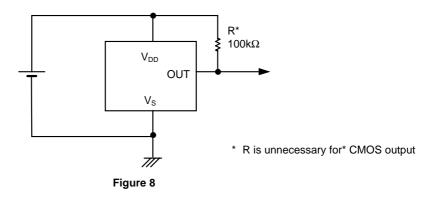
5. Oscillation

In applications where a resistor is connected to the voltage detector input (Figure 7), in the CMOS active low products for example, the through-type current generated when the output goes from low to high (release) causes a voltage drop equal to [through-type current]×[input resistance] across the resistor. When the resultant input voltage drops below the detection voltage -V_{DET}, the output voltage returns to its low level. In this state, the through-type current and its resultant voltage drop have disappeared, and the output goes back from low to high. A through-type current is again generated, a voltage drop appears, and the process repeats. This unstable condition is referred to as oscillation.

· Misimplementation with input voltage divider



■ Standard Circuit



Operation

- 1. Basic operation: CMOS active low output
 - (1) When power supply voltage V_{DD} is greater than the release voltage +V_{DET}, the Nch transistor is OFF and the Pch transistor ON, causing V_{DD} (high) to appear at the output. With the Nch transistor N1 of Figure 9 OFF, the comparator input voltage is (RB+RC)/(RA+RB+RC)×V_{DD}.
 - (2) When power supply voltage V_{DD} goes below +V_{DET}, the output maintains the power supply voltage level, as long as V_{DD} remains above the detection voltage -V_{DET}. When V_{DD} does fall below -V_{DET} (A in Figure 10), the Nch transistor goes ON, the Pch transistor goes OFF, and V_{SS} appears at the output. With the Nch transistor N 1 of Figure 9 ON, the comparator input voltage is RB/(RA+RB) ×V_{DD}.
 - (3) When V_{DD} falls below the minimum operating voltage, the output becomes undefined. However, output will revert to V_{DD} if a pull-up has been employed.
 - (4) V_{SS} will again be output when V_{DD} rises above the minimum operating voltage. V_{SS} will continue to be output even when V_{DD} surpasses - V_{DET} , as long as it does not exceed the release voltage + V_{DET} .
 - (5) When V_{DD} rises above + V_{DET} (B in Figure 10), the Nch transistor goes OFF, the Pch transistor goes ON, and V_{DD} appears at the output.

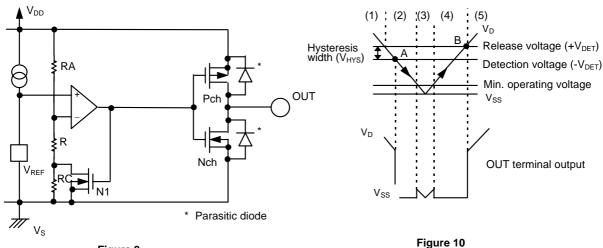


Figure 9

2. Other characteristics

(1) Temperature characteristic of detection voltage

The temperature characteristics of the detection voltage are expressed by the oblique line parts in Figure 11.

S-80815AXNP:

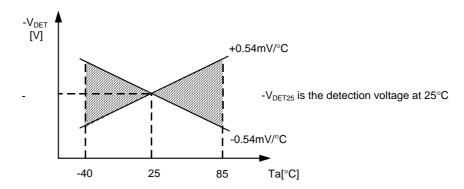


Figure 11

(2) Temperature characteristics of release voltage

The temperature factor $\left(\frac{\Delta + V_{DET}}{\Delta Ta}\right)$ of the release voltage is calculated by the temperature factor of the detection voltage as follows:

$$\frac{\Delta + V_{DET}}{\Delta Ta} = \frac{+V_{DET}}{-V_{DET}} \times \frac{\Delta - V_{DET}}{\Delta Ta}$$

The temperature factor of the release voltage has a same sign characteristics as the temperature factor of the detection voltage.

(3) Temperature characteristics of hysteresis voltage

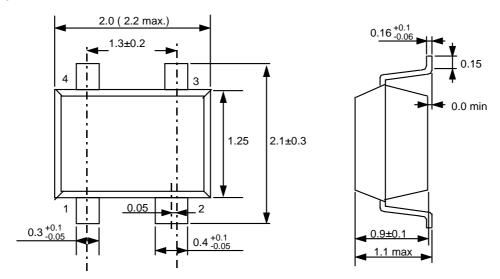
The temperature characteristics of hysteresis voltage $\left(\frac{\Delta + V_{DET}}{\Delta Ta} - \frac{\Delta - V_{DET}}{\Delta Ta}\right)$ is calculated as

$$\frac{\Delta + V_{DET}}{\Delta Ta} \; - \; \frac{\Delta - V_{DET}}{\Delta Ta} \; = \frac{V_{HY}}{-V_{DET}} \; \times \; \frac{\Delta - V_{DET}}{\Delta Ta}$$

Remark: An example of temperature characteristics of (1) to (3) is shown on pages 21 and 22.

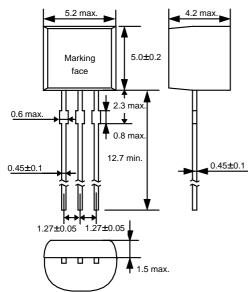
Dimensions

(1) SC-82AB

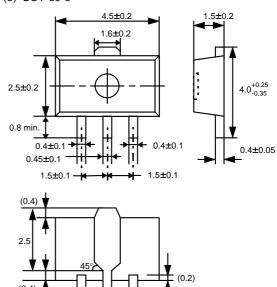


The surface of lead wire is plated or dipped with solder.

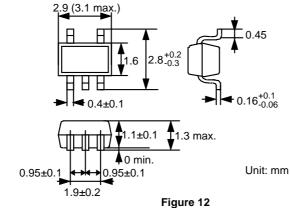




(3) SOT-89-3



(4) SOT-23-5



■ Taping

1.SC-82AB

1.1 Tape specifications

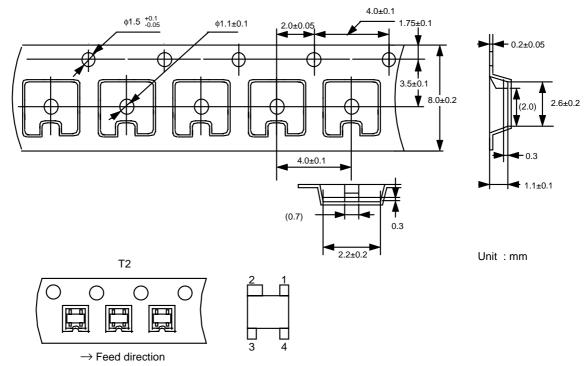
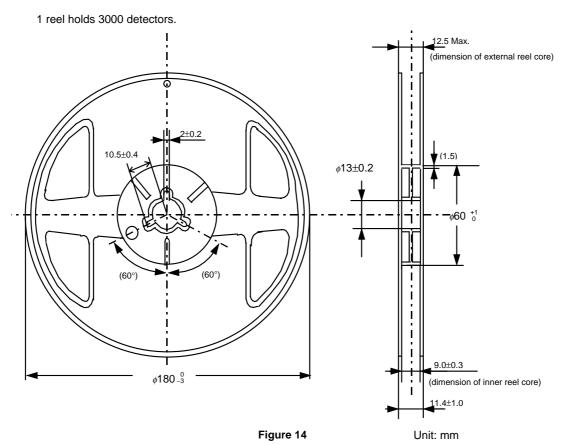


Figure 13

1.2 Reel specifications



Seiko Instruments Inc.

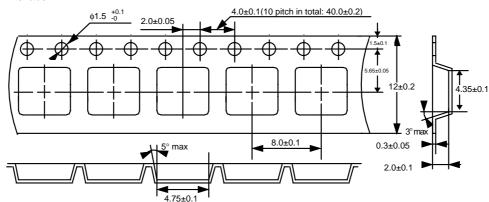
2. SOT-89-3

2.1 Tape specifications

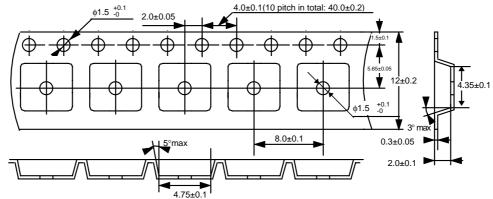
There are two color (white and blue) labels depending upon the presence of holes at center of the emboss.

Two types of tape (T1 and T2) are available depending upon the direction of the IC on the tape.

(1) White label



(2) Blue label



Unit: mm

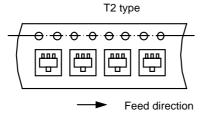
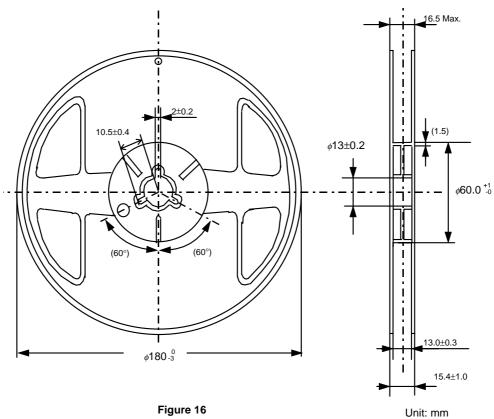


Figure 15

2.2 Reel specifications

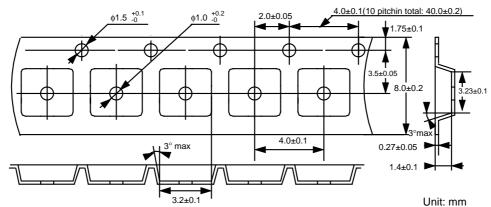
1 reel holds 1000 detectors.



3. SOT-23-5

3.1 Tape specifications

The emboss cover tape comes in two tones (milk white/transparent and transparent).



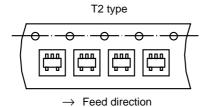
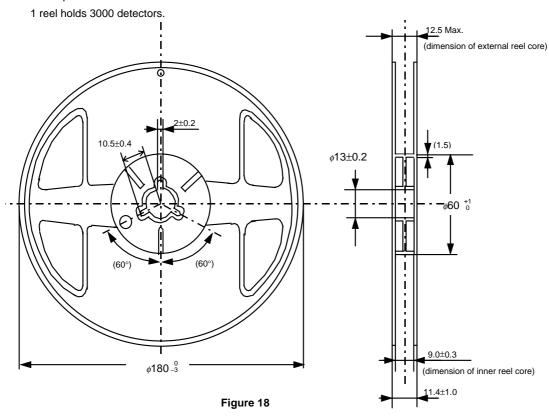
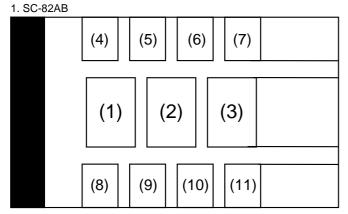


Figure 17

3.2 Reel Specifications



■ Marking



- (1) to (3) Product name (abbreviation) (4) to (11) Lot No. (indicated by dots)
- 3. SOT-89-3

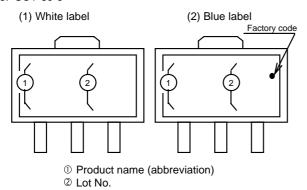
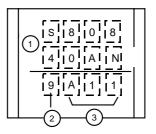


Figure 19

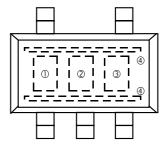
2. TO-92

Unit: mm



- ① Product name
- ② Last digit of the year
- 3 Lot No.

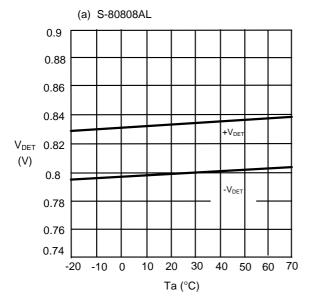
4. SOT-23-5

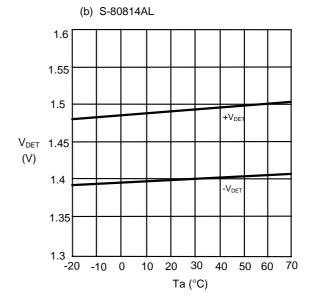


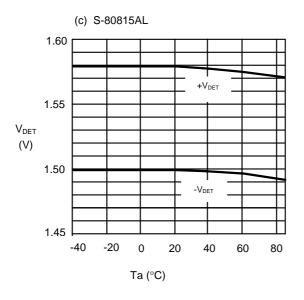
- ① and ② Product name (abbreviation)
- 3 and 4 Lot No.
 - 3: Alphabet
 - Dot on one side

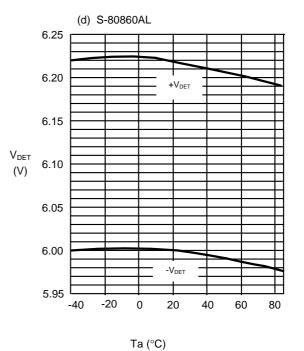
■ Characteristics (typical characteristics)

(1) Detection voltage (V_{DET}) - Temperature (Ta)

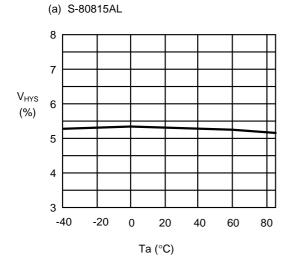


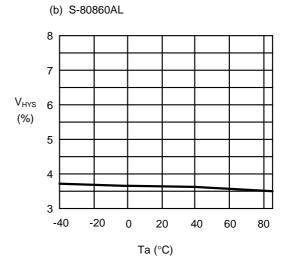




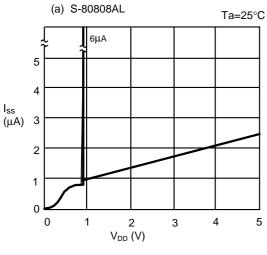


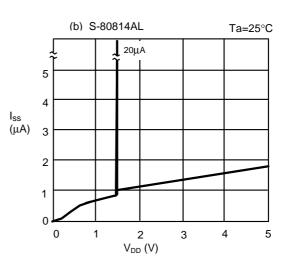
(2) Hysteresis voltage width (V_{HYS}) - Temperature (Ta)

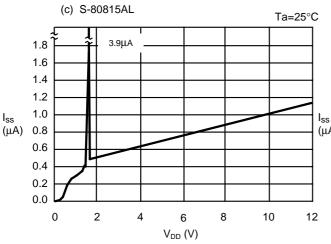


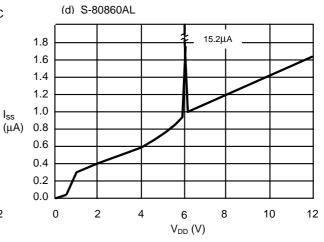


(3) Current consumption (I_{SS}) - Input voltage (V_{DD})

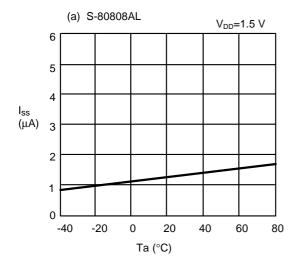


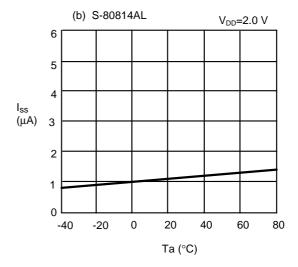


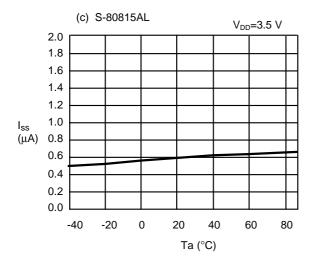


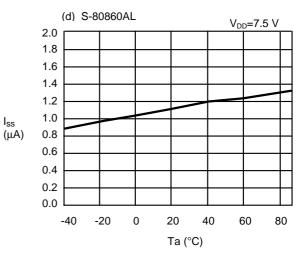


(4) Current consumption (I_{SS}) - Temperature (Ta)

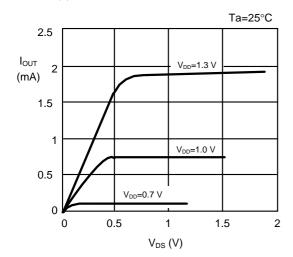




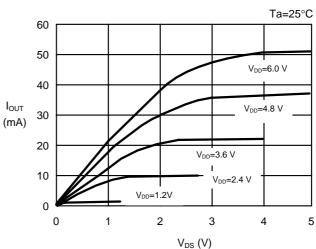




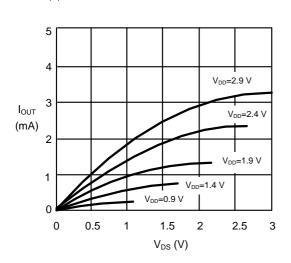
- (5) Nch transistor output current (I_{OUT}) V_{DS}
 - (a) S-80814AL



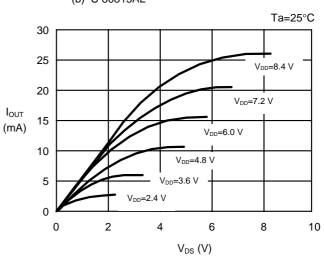
(b) S-80860AL



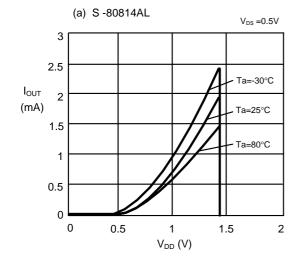
- (6) Pch transistor output current (I_{OUT}) V_{DS}
 - (a) S-80808AL

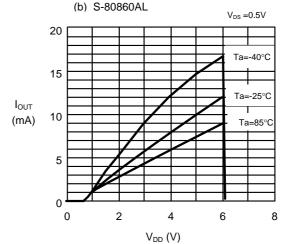


(b) S-80815AL

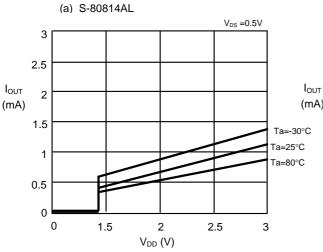


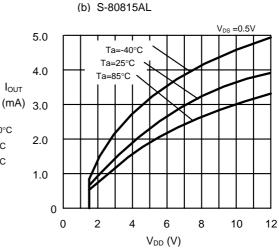
(7) Nch transistor output current (I_{OUT}) - Input voltage(V_{DD})



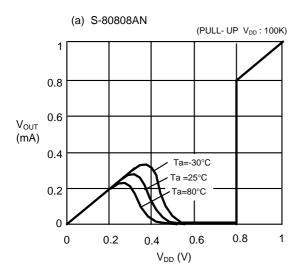


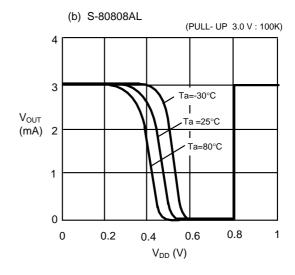
(8) Pch transistor output current(I_{OUT}) - Input voltage(V_{DD})

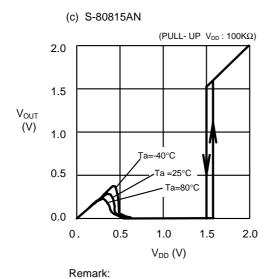




(9) Minimum operating voltage



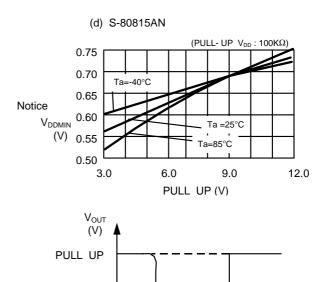




 V_{DDMIN} is defined with V_{DD} when V_{OUT} goes

in Figure 20 when raising V_{DD} from 0 V.

below 10% of the PULL UP voltage as shown

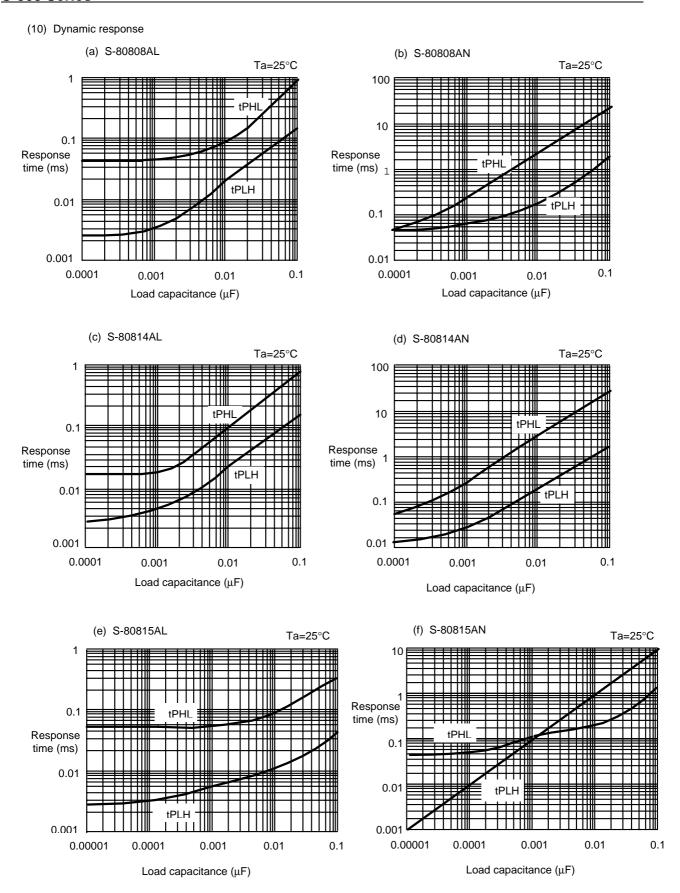


 V_{DDMIN}

Figure 20

PULL UP×0.1

V_{DD} (V)



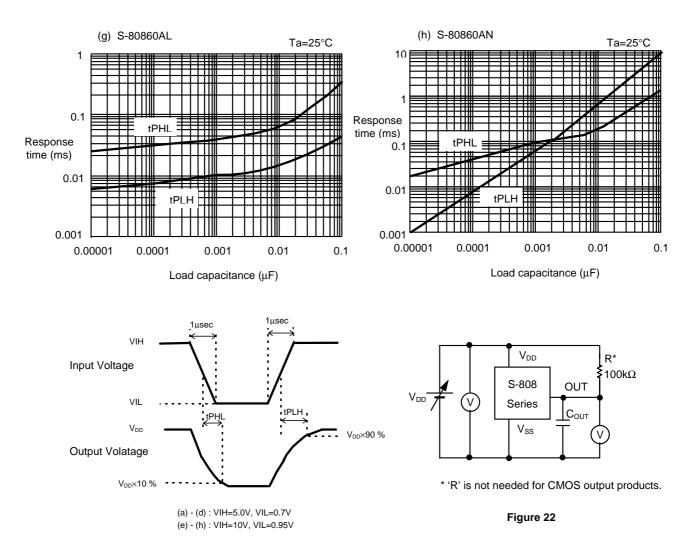


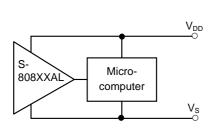
Figure 21

■ Application Circuit Examples

1. Microcomputer reset circuits

If the power supply voltage to a microcomputer falls below the specified level, an unspecified operation may be performed or the contents of the memory register may be lost. When power supply voltage returns to normal, the microcomputer needs to be initialized before normal operations can be done.

Reset circuits protect microcomputers in the event of current being momentarily switched off or lowered. With the S-808 Series which has a low operating voltage, a high-precision detection voltage and hysteresis characteristic, the reset circuits shown in Figures 19 to 20 can be easily constructed.



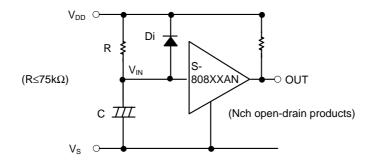
V_{DD1} V_{DD2}
S808XXAN Microcomputer
(Nch open-drain output products only)

Figure 23

Figure 24

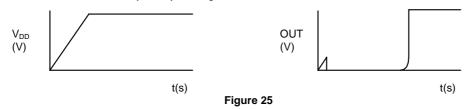
2. Addition of power-on reset circuit

A power-on reset circuit can be constructed using Nch open-drain product of S-808 Series.



Note 1: R should be 75 k Ω or less for purpose of protection against oscillation.

Note 2: Di instantaneously discharges the electric charge stored by C at the falling of the power. Di is not necessary if delay in falling time is normal.



Note 3: When the power steeply rises, output may goes high for a instant due to the IC inconstant region characteristics (output voltage is unstable in the region under minimum operating voltage) as shown in Figure. 26.

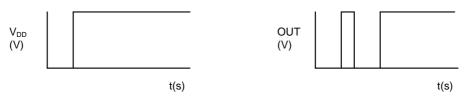
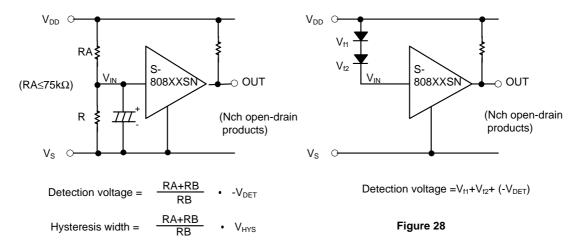


Figure 26

3. Change of detection voltage

<u>In Nch open-drain output products of the S-808 Series</u>, detection voltage can be changed using resistance dividers or diodes as shown in Figures 27 and 28. In Figure 27, hysteresis width is also changed.



Note1: If RA and RB are large, the hysteresis width may be larger than the value given by the formula above due to through-type current (which flows slightly in Nch open-drain circuit).

Note2: RA should be $75k\Omega$ or less for purpose of protection against oscillation.

Figure 27

Remarks

- In CMOS output products of the S-808 Series, through-type current flows when the device is detecting or releasing. If a high impedance is connected to the input, oscillation may be caused due to the fall of the voltage by the through-type current when lowering the voltage during releasing.
- When designing for mass production using an application circuit described herein, take the product deviation and temperature characteristic into consideration.
- Seiko Instruments Inc. shall not bear any responsibility for the patents on the circuits described herein.

Collection of Product FAQs

Author: Imura Yukihiro Date: 99/05/27 (Thurday) 13:43 (Modified: 99/05/28 (Friday) 09:55)

<Information level>

A: Public (Printing O.K.)

Index: A: General

<Product>

Division name: 01 IC

Category 1: 11 Power Supply

Category 2: 1. Voltage Detectors

Cal No.: S-808

Related Documents:

Question:

What is the table for S-8053/S-8054 series to S-808 series replacement?

Answer:

Use the following table as a guide

Type Upper Line:S-805		Detection Voltage (V)			Release Voltage (V)			Operati	on Volta	ge (V)	
Lower Line: S-808	Package	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Point to be noted
S-8053ALB	TO-92	2.795	2.950	3.105	2.851	3.098	3.353	1.6	_	10.0	
S-80829ALY	TO-92	2.842	2.900	2.958	2.927	3.045	3.195	0.95	_	10.0	
S-8053ALB-LI	SOT-89-3	2.795	2.950	3.105	2.851	3.098	3.353	1.6	_	10.0	
S-80829ALUP-EAS	SOT-89-3	2.842	2.900	2.958	2.927	3.045	3.195	0.95	_	10.0	
S-8053HLB	TO-92	2.895	3.000	3.105	2.953	3.150	3.353	1.6	_	10.0	
S-80830ALY	TO-92	2.940	3.000	3.060	3.028	3.150	3.305	0.95	_	10.0	
S-8053HNB	TO-92	2.895	3.000	3.105	2.953	3.150	3.353	1.6	_	10.0	
S-80830ANY	TO-92	2.940	3.000	3.060	3.028	3.150	3.305	0.95	_	10.0	
S-8053ALR	TO-92	3.095	3.250	3.405	3.157	3.413	3.677	1.6	_	10.0	
S-80832ALY	TO-92	3.136	3.200	3.264	3.230	3.360	3.525	0.95	_	10.0	

S-8053ALR-LJ	SOT-89-3	3.095	3.250	3.405	3.157	3.413	3.677	1.6	_	10.0	
S-80832ALUP-EAW	SOT-89-3	3.136	3.200	3.264	3.230	3.360	3.525	0.95	_	10.0	
	·										
S-8053ANO	TO-92	3.395	3.550	3.705	3.463	3.728	4.001	1.6	_	10.0	
S-80835ANY	TO-92	3.430	3.500	3.570	3.533	3.675	3.856	0.95	_	10.0	
									•		
S-8054ALB	TO-92	3.995	4.150	4.305	4.075	4.358	4.649	1.6	_	10.0	
S-80841ALY	TO-92	4.018	4.100	4.182	4.139	4.305	4.517	0.95	_	10.0	
	·										
S-8054ALB-LM	SOT-89-3	3.995	4.150	4.305	4.075	4.358	4.649	1.6	_	10.0	
S-80841ALUP-EA5	SOT-89-3	4.018	4.100	4.182	4.139	4.305	4.517	0.95	_	10.0	
	·										
S-8054ALR	TO-92	4.295	4.450	4.605	4.381	4.673	4.973	1.6	_	10.0	
S-80844ALY	TO-92	4.312	4.400	4.488	4.441	4.620	4.847	0.95	_	10.0	
S-8054ALR-LN	SOT-89-3	4.295	4.450	4.605	4.381	4.673	4.973	1.6	_	10.0	
S-80844ALUP-EA8	SOT-89-3	4.312	4.400	4.488	4.441	4.620	4.847	0.95	_	10.0	
S-8054ALO	TO-92	4.595	4.750	4.905	4.687	4.988	5.297	1.6	_	10.0	
S-80847ALY	TO-92	4.606	4.700	4.794	4.744	4.935	5.178	0.95	_	10.0	
S-8054ALO-LO	SOT-89-3	4.595	4.750	4.905	4.687	4.988	5.297	1.6	_	10.0	
S-80847ALUP-EEB	SOT-89-3	4.606	4.700	4.794	4.744	4.935	5.178	0.95	_	10.0	
S-8054ALY	TO-92	4.895	5.100	5.205	4.993	5.355	5.621	1.6	_	10.0	
S-80851ALY	TO-92	4.998	5.100	5.202	5.148	5.355	5.618	0.95	_	10.0	
S-8054ALY-LP	SOT-89-3	4.895	5.100	5.205	4.993	5.355	5.621	1.6	_	10.0	
S-80851ALUP-EEF	SOT-89-3	4.998	5.100	5.202	5.148	5.355	5.618	0.95	_	10.0	
S-8054HN	TO-92	3.800	4.000	4.200	3.876	4.200	4.536	1.6	_	10.0	
S-80839ANY	TO-92	3.822	3.900	3.978	3.937	4.095	4.296	0.95	_	10.0	
							1				
S-8054HN-CB	SOT-89-3	3.800	4.000	4.200	3.876	4.200	4.536	1.6	_	10.0	
S-80839ANUP-ED3	SOT-89-3	3.822	3.900	3.978	3.937	4.095	4.296	0.95	_	10.0	
·		·	·	·	·	·				_	

S-8054HNM	TO-92	4.500	4.600	4.700		4.650	4.800	1.6	_	10.0	
S-80846ANY	TO-92	4.508	4.600	4.692	4.643	4.830	5.067	0.95	_	10.0	Max. value of release voltage
S-80845ANY	TO-92	4.410	4.500	4.590	4.542	4.725	4.957	0.95	_	10.0	Max. value of release voltage
S-80844ANY	TO-92	4.312	4.400	4.488	4.441	4.620	4.847	0.95	_	10.0	Min. value of detection voltage
S-8054HNM-CQ	SOT-89-3	4.500	4.600	4.700		4.650	4.800	1.6		10.0	
S-80846ANUP-EJA	SOT-89-3	4.508	4.600	4.692	4.643	4.830	5.067	0.95	_	10.0	Max. value of release voltage
S-80845ANUP-ED9	SOT-89-3	4.410	4.500	4.590	4.542	4.725	4.957	0.95	_	10.0	Max. value of release voltage
S-80844ANUP-ED8	SOT-89-3	4.312	4.400	4.488	4.441	4.620	4.847	0.95	_	10.0	Min. value of detection voltage

The production of the S8054HNM will be continued, but this product cannot be newly employed.

<Remarks>

FAQ No.: 11S808002

Collection of Product FAQs

Author: Imura Yukihiro Date: 99/05/27 (Thursday) 13:12 (Modified: 99/05/27 (Thursday) 13:37)

<Information level>

A: Public (Printing O.K.)

Index: A: General

<Product>

Division name: 01 IC

Category 1: 11 Power Supply

Category 2: 1. Voltage Detectors

Cal No.: S-808

Related Documents:

Question:

What is the table for S-8051/S-8052 series to S-808 series replacement?

Answer:

Use the following table as a guide.

		_	Dotoo	tion \/olto	~~ (\ (\)	Doloo	aa Valta	~~ (\ (\	Onorot	ion Val	to as (\/)	
Type	Upper Line: S-805		Detec	tion Volta	ige (v)	Relea	se Volta	ge (v)	Operat	ion voi	tage (V)	
	Lower Line: S-808	Package	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Point to be noted
S-805	1ANB	TO-92	0.995	1.050	1.105	1.015	1.103	1.193	0.9	_	5.0	
S-808	10ANNP-E70	SC-82AB	0.980	1.000	1.020	1.017	1.054	1.091	0.7	_	5.0	Difference in package
		•										
S-805	1ANB-NA	SOT-89-3	0.995	1.050	1.105	1.015	1.103	1.193	0.9	_	5.0	
S-808	10ANNP-E70	SC-82AB	0.980	1.000	1.020	1.017	1.054	1.091	0.7	_	5.0	Difference in package
		•										
S-805	1ANR	TO-92	1.095	1.150	1.205	1.117	1.208	1.301	1.0	_	5.0	
S-808	11ANNP-E71	SC-82AB	1.078	1.100	1.122	1.125	1.164	1.203	0.7	_	5.0	Difference in package
S-805	1ANR-NB	SOT-89-3	1.095	1.150	1.205	1.117	1.208	1.301	1.0	_	5.0	
S-808	11ANNP-E71	SC-82AB	1.078	1.100	1.122	1.125	1.164	1.203	0.7	_	5.0	Difference in package
S-805	1HN-CD	SOT-89-3	1.795	1.900	2.005	1.831	1.995	2.165	1.5	_	10.0	
S-808	19ANUP-EDG	SOT-89-3	1.862	1.900	1.938	1.918	1.995	2.093	0.95	_	10.0	

S-8052ANB-NE	SOT-89-3	1.995	2.100	2.205	2.035	2.205	2.381	1.5		10.0	
S-80821ANUP-EDJ	SOT-89-3	2.058	2.100	2.142	2.120	2.205	2.313	0.95	_	10.0	
S-8052ALB	TO-92	1.995	2.100	2.205	2.035	2.205	2.381	1.5		10.0	
S-80821ALY	TO-92	2.058	2.100	2.142	2.120	2.205	2.313	0.95	_	10.0	
S-8052ALB-LE	SOT-89-3	1.995	2.100	2.205	2.035	2.205	2.381	1.5		10.0	
S-80821ALUP-EAJ	SOT-89-3	2.058	2.100	2.142	2.120	2.205	2.313	0.95		10.0	
S-8052ALR	TO-92	2.195	2.300	2.405	2.239	2.415	2.597	1.5		10.0	
S-80823ALY	TO-92	2.254	2.300	2.346	2.322	2.415	2.534	0.95		10.0	
S-8052ALR-LF	SOT-89-3	2.195	2.300	2.405	2.239	2.415	2.597	1.5	_	10.0	
S-80823ALUP-EAL	SOT-89-3	2.254	2.300	2.346	2.322	2.415	2.534	0.95	_	10.0	
S-8052ALO	TO-92	2.395	2.500	2.605	2.443	2.625	2.813	1.5	_	10.0	
S-80825ALY	TO-92	2.450	2.500	2.550	2.524	2.625	2.754	0.95	_	10.0	
S-8052ALO-LG	SOT-89-3	2.395	2.500	2.605	2.443	2.625	2.813	1.5	_	10.0	
S-80825ALUP-EAN	SOT-89-3	2.450	2.500	2.550	2.524	2.625	2.754	0.95	_	10.0	
		_									
S-8052ALY	TO-92	2.595	2.700	2.805	2.647	2.835	3.029	1.5	_	10.0	
S-80827ALY	TO-92	2.646	2.700	2.754	2.725	2.835	2.974	0.95	_	10.0	
	1	1	1	T		ı					
S-8052ALY-LH	SOT-89-3	2.595	2.700	2.805	2.647	2.835	3.029	1.5	_	10.0	
S-80827ALUP-EAQ	SOT-89-3	2.646	2.700	2.754	2.725	2.835	2.974	0.95	_	10.0	
	1	1	1	T		ı					
S-8052ANY-NH	SOT-89-3	2.595	2.700	2.805	2.647	2.835	3.029	1.5	—	10.0	
S-80827ANUP-EDQ	SOT-89-3	2.646	2.700	2.754	2.725	2.835	2.974	0.95	—	10.0	
		1							ı		
S-8052HNM	TO-92	2.295	2.400	2.505	4.300	4.400	4.500	1.5	_	10.0	
S-80824ANY	TO-92	2.352	2.400	2.448	2.423	2.520	2.644	0.95	—	10.0	Release voltage
		1	ı	ı		ı		T	T		T
S-8052HNM-CR	SOT-89-3	2.295	2.400	2.505	4.300	4.400	4.500	1.5	_	10.0	
S-80824ANUP-EDM	SOT-89-3	2.352	2.400	2.448	2.423	2.520	2.644	0.95	_	10.0	Release voltage

The production of the S8052HNM will be continued, but this product cannot be newly employed.

<Remarks>

FAQ No.: 11S808001